

#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2kV
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 standards for High Reliability

#### **Mechanical Data**

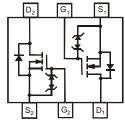
- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
  Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)





Top View





**Bottom View** 

Top View Internal Schematic

### Ordering Information (Note 3)

Part Number	Case	Packaging
DMN2400UV-7	SOT-563	3,000/Tape & Reel
DMN2400UV-13	SOT-563	10,000/Tape & Reel

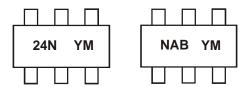
SOT-563

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com.

### **Marking Information**



24N and NAB = Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Χ		Υ		Z	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

January 2011



# Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characterist	ic		Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	20	V
Gate-Source Voltage			$V_{GSS}$	±12	V
Continuous Drain Current (Note 4) Steady $T_A = 25$ °C State $T_A = 85$ °C		I <sub>D</sub>	1.33 0.84	А	
Pulsed Drain Current			I <sub>DM</sub>	3	Α

## Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	$P_{D}$	530	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	233.8	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

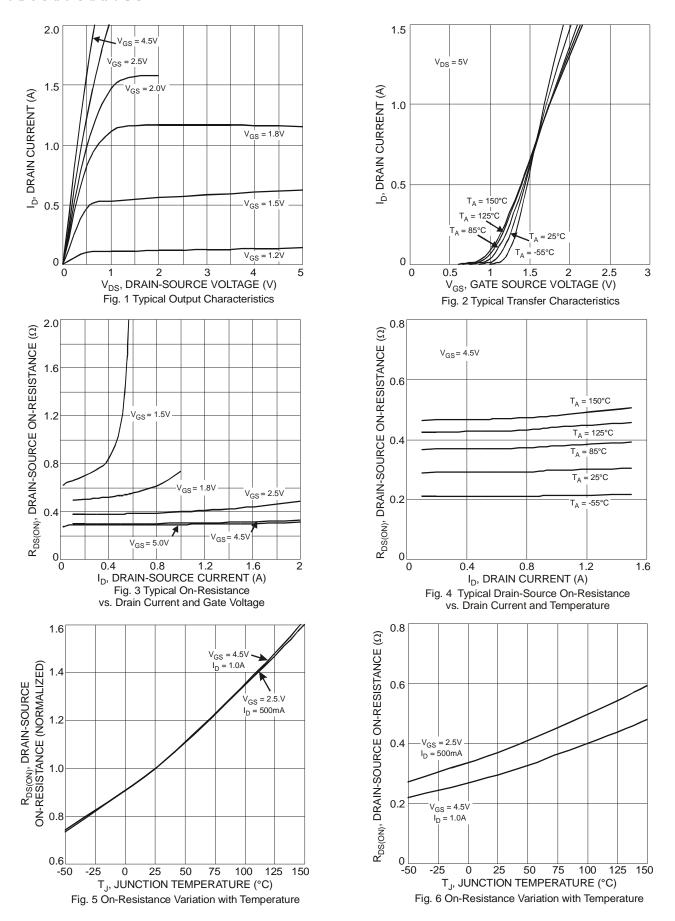
### Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	100	nA	$V_{DS} = 20V, V_{GS} = 0V$
Cata Cauraa Laakaga		-	-	±1.0	μА	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$
Gate-Source Leakage	I <sub>GSS</sub>	ı	-	±50		$V_{GS} = \pm 10V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)				-		
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	-	0.9	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
		1	0.3	0.48		$V_{GS} = 5.0V, I_D = 200mA$
		1	0.35	0.5		$V_{GS} = 4.5V, I_D = 600mA$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	0.45	0.7	Ω	$V_{GS} = 2.5V, I_D = 500mA$
	, ,	-	0.55	0.9		$V_{GS} = 1.8V, I_D = 350mA$
		-	0.65	1.5		$V_{GS} = 1.5V, I_D = 50mA$
Forward Transfer Admittance	Y <sub>fs</sub>	-	1.4	-	S	$V_{DS} = 10V, I_D = 400mA$
Diode Forward Voltage (Note 5)	$V_{SD}$		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA,$ f = 1.0MHz
DYNAMIC CHARACTERISTICS (Note 6)	•				l.	
Input Capacitance	C <sub>iss</sub>	-	36.0	-	pF	.,
Output Capacitance	Coss	-	5.7	-	pF	$V_{DS} = 16V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	-	4.2	-	pF	
Gate Resistance	Rg	-	68	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ ,
Total Gate Charge	Qq	-	0.5	-	nC	V <sub>GS</sub> =4.5V, V <sub>DS</sub> = 10V,
Gate-Source Charge	Q <sub>gs</sub>	-	0.07	-	nC	I <sub>D</sub> =250mA
Gate-Drain Charge	Q <sub>gd</sub>	-	0.1	-	nC	7
Turn-On Delay Time	t <sub>D(on)</sub>	-	4.06	-	ns	101/11/
Turn-On Rise Time	t <sub>r</sub>	-	7.28	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t <sub>D(off)</sub>		13.74	-	ns	$R_L = 47\Omega$ , $R_G = 10\Omega$ , $R_D = 200$ mA
Turn-Off Fall Time	t <sub>f</sub>	1	10.54	-	ns	ID = ZUUIIIA

Notes:

- 4. Device soldered onto FR-4 PCB, minimum recommended soldering pad dimensions (25.4mm x 25.4mm x1.6mm, 2oz Cu pad: 0.18mm² x 6).
- 5. Short duration pulse test used to minimize self-heating effect.6. Guaranteed by design. Not subject to product testing.







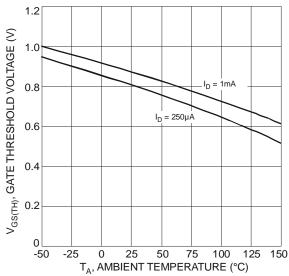
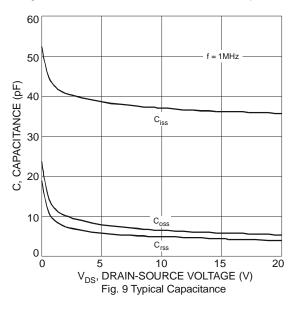
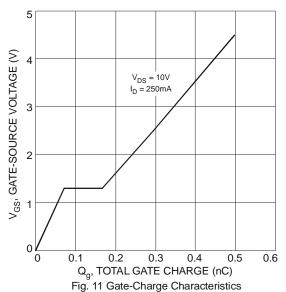
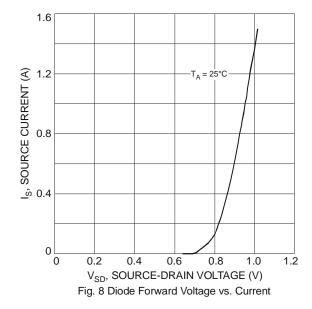
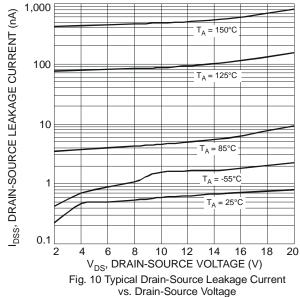


Fig. 7 Gate Threshold Variation vs. Ambient Temperature











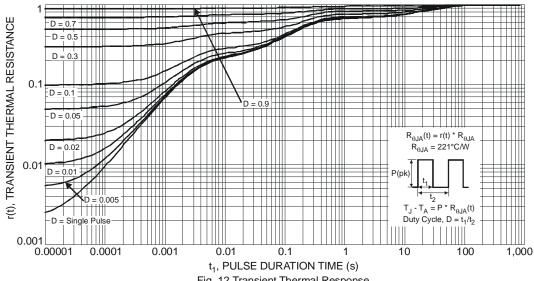
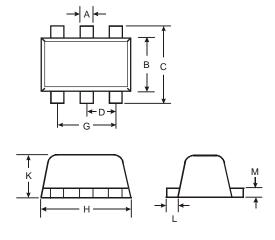


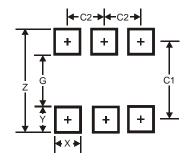
Fig. 12 Transient Thermal Response

## **Package Outline Dimensions**



SOT-563							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
O	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	0.55	0.60	0.60				
L	0.10	0.30	0.20				
M	0.10	0.18	0.11				
All Dimensions in mm							

## **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5



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